Diode

Name VRRM[V] VF[V] trr[ns] Cd[pF] Material

DHG10I1200PM 1200 3.06 75 4 Si

STPSC10H065G2 650 1.95 Schottky 55 SiC

MOSFET

Name VGS,th(V) VDS(V) Id(A) RDS,ON(Ω) Qg(nC)

NTHL190N65S3HF 4 650 20 0.190 34

SiHP22N60AE 3 650 20 0.156 96

Various

VGS,th(V) VDS(V) Id(A) RDS,ON(Ω) Qg(nC)

MOS: Si7454FDP 1-3 100 23.5 0.034 8

GaN: GS61004B 0-6 100 38 0.016 3.3

IGBT: STGYA120M65DF2AG 6 650 120 420

SiC: UF3C065080B7S 2.8 650 145 0.018 283